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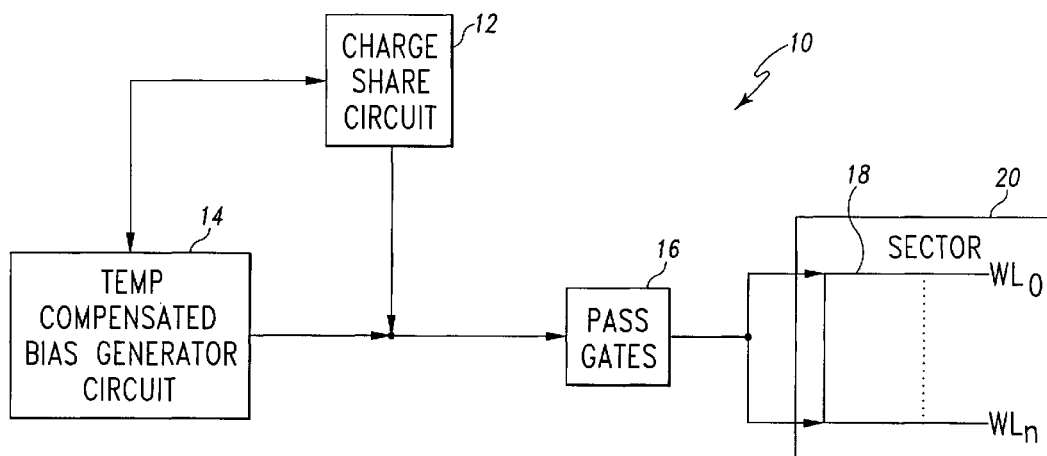
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(54) Title: TEMPERATURE-COMPENSATED BIAS GENERATOR



(57) Abstract: The present invention discloses methods and systems for generating a bias voltage during an Automatic Program Disturb Erase Verify (APDEV) operation in a memory device. During the APDEV operation, a predetermined supply voltage is generated by a regulated power supply. The predetermined supply voltage is directed to a temperature-compensated bias generator circuit (14). The temperature-compensated bias generator circuit (14) is activated to generate the bias voltage based on the operating temperature of the memory device.